# Advance Information

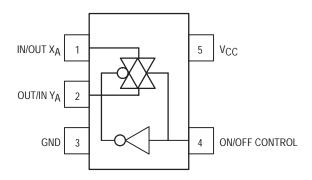
# **Analog Switch**

The MC74VHC1G66 is an advanced high speed CMOS bilateral analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. This bilateral switch controls analog and digital voltages that may vary across the full power–supply range (from  $V_{CC}$  to GND).

The MC74VHC1G66 is compatible in function to a single gate of the High Speed CMOS MC74VHC4066 and the metal–gate CMOS MC14066. The device has been designed so that the ON resistances ( $R_{ON}$ ) are much lower and more linear over input voltage than  $R_{ON}$  of the metal–gate CMOS or High Speed CMOS analog switches.

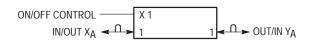
The ON/OFF control inputs are compatible with standard CMOS outputs; with pull-up resistors, it is compatible with LSTTL outputs.

- High Speed: tpD = TBD (Typ) at VCC = 5 V
- Low Power Dissipation:  $I_{CC} = 2 \mu A \text{ (Max)}$  at  $T_A = 25^{\circ}\text{C}$
- Diode Protection Provided on Inputs and Outputs
- Improved Linearity and Lower ON Resistance over Input Voltage than the MC14066 or the HC4066
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; MM > 200 V, CDM > 1500 V
- Chip Complexity: 11 FETs or 3 Equivalent Gates



5-Lead SOT-353 Pinout (Top View)

#### LOGIC SYMBOL





#### ON Semiconductor

Formerly a Division of Motorola http://onsemi.com



SC-88A / SOT-353 DF SUFFIX CASE 419A

#### **MARKING DIAGRAM**



PIN ASSIGNMENT						
1	IN/OUT X <sub>A</sub>					
2 OUT/IN Y <sub>A</sub>						
3	GND					
4	ON/OFF CONTROL					
5	VCC					

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

#### **FUNCTION TABLE**

State of Analog Switch
Off
On

This document contains information on a new product. Specifications and information herein are subject to change without notice.

#### **ABSOLUTE MAXIMUM RATINGS**

Characteristics	Symbol	Value	Unit
DC Supply Voltage	Vcc	-0.5 to +7.0	V
Digital Input Voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> +0.5	V
Analog Output Voltage	V <sub>IS</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Digital Input Diode Current	lικ	-20	mA
DC Supply Current, V <sub>CC</sub> and GND	lcc	+25	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

<sup>†</sup>Derating — SC–88A Package: –3 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	Vcc	4.5	5.5	V
Digital Input Voltage	V <sub>IN</sub>	GND	Vcc	V
Analog Input Voltage	VIS	GND	Vcc	V
Static or Dynamic Voltage Across Switch	V <sub>IO</sub> *		1.2	V
Operating Temperature Range	TA	<del>-</del> 55	+85	°C
Input Rise and Fall Time ON/OFF Control Input $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t <sub>r</sub> , t <sub>f</sub>	0 0	100 20	ns/V

<sup>\*</sup> For voltage drops across the switch greater than 1.2V (switch on), excessive V<sub>CC</sub> current may be drawn; i.e. the current out of the switch may contain both V<sub>CC</sub> and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

#### DC ELECTRICAL CHARACTERISTICS

			VCC	Т	A = 25°0	2	T <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High–Level Input Voltage ON/OFF Control Input	R <sub>ON</sub> = Per Spec	2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low–Level Input Voltage ON/OFF Control Input	R <sub>ON</sub> = Per Spec	2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
I <sub>IN</sub>	Maximum Input Leakage Current ON/OFF Control Input	V <sub>IN</sub> = V <sub>CC</sub> or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
lcc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $V_{IO} = 0V$	5.5			2.0		20		40	μΑ
RON	Maximum "ON" Resistance	$V_{IN} = V_{IH}$ $V_{IS} = V_{CC}$ or GND $ I_{IS}  \le 10$ mA (Figure 1)	3.0 4.5 5.5		30 20 15	50 30 20		70 40 35		100 50 45	Ω
		Endpoints $V_{IN} = V_{IH}$ $V_{IS} = V_{CC}$ or GND $ I_{IS}  \le 10$ mA (Figure 1)	3.0 4.5 5.5		25 12 8	50 20 15		65 26 23		90 40 32	Ω
loff	Maximum Off–Channel Leakage Current	V <sub>IN</sub> = V <sub>IL</sub> V <sub>IS</sub> = V <sub>CC</sub> or GND Switch Off (Figure 2)	5.5			0.1		0.5		1.0	μΑ
ION	Maximum On–Channel Leakage Current	V <sub>IN</sub> = V <sub>IH</sub> V <sub>IS</sub> = V <sub>CC</sub> or GND Switch On (Figure 3)	5.5			0.1		0.5		1.0	μΑ

### AC ELECTRICAL CHARACTERISTICS ( $C_{load}$ = 50 pF, Input $t_r/t_f$ = 3.0ns)

			VCC	ī	T <sub>A</sub> = 25°(	<b>C</b>	T <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
<sup>t</sup> PLH <sup>,</sup> <sup>t</sup> PHL	Maximum Propogation Delay, Input X to Y	Y <sub>A</sub> = Open Figure 4	2.0 3.0 4.5 5.5		1 0 0 0	5 2 1 1		6 3 1 1		7 4 2 1	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propogation Delay, ON/OFF Control to Analog Output	$R_L$ = 1000 $Ω$ Figure 5	2.0 3.0 4.5 5.5		15 8 6 4	35 15 10 7		46 20 13 9		57 25 17 11	ns
<sup>t</sup> PZL <sup>,</sup> <sup>t</sup> PZH	Maximum Propogation Delay, ON/OFF Control to Analog Output	$R_L$ = 1000 $Ω$ Figure 5	2.0 3.0 4.5 5.5		15 8 6 4	35 15 10 7		46 20 13 9		57 25 17 11	ns
C <sub>IN</sub>	Maximum Input	ON/OFF Control Input	0.0		3	10		10		10	pF
	Capacitance	Contol Input = GND Analog I/O Feedthrough	5.0		4 4	10 10		10 10		10 10	

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note NO TAG)	18	pF

<sup>1.</sup>  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_{D} = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .

#### ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Test Conditions	vcc	Limit 25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response Figure 7	$f_{in}$ = 1 MHz Sine Wave Adjust $f_{in}$ voltage to obtain 0 dBm at VOS Increase $f_{in}$ = frequency until dB meter reads –3dB R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 10 pF	3.0 4.5 5.5	150 175 200	MHz
ISO <sub>off</sub>	Off-Channel Feedthrough Isolation Figure 8	$f_{in}$ = Sine Wave Adjust $f_{in}$ voltage to obtain 0 dBm at $V_{IS}$ $f_{in}$ = 10 kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50 pF	3.0 4.5 5.5	-50 -50 -50	dB
		$f_{in} = 1.0 \text{ kHz}, R_L = 50\Omega, C_L = 10 \text{ pF}$	3.0 4.5 5.5	-40 -40 -40	
NOISE <sub>feed</sub>	Feedthrough Noise Control to Switch Figure 9	$V_{in} \le 1$ MHz Square Wave ( $t_{\Gamma} = t_{f} = 2ns$ ) Adjust R <sub>L</sub> at setup so that $I_{S} = 0$ A R <sub>L</sub> = $600\Omega$ , C <sub>L</sub> = $50$ pF	3.0 4.5 5.5	45 60 130	mVpp
		$R_L = 50\Omega$ , $C_L = 10 pF$	3.0 4.5 5.5	25 30 60	
THD	Total Harmonic Distortion Figure 10	$f_{in}$ = 1 kHz, R <sub>L</sub> = 10k $\Omega$ , C <sub>L</sub> = 50 pF THD = THD <sub>Measured</sub> - THD <sub>Source</sub> V <sub>IS</sub> = 3.0 Vpp sine wave V <sub>IS</sub> = 4.0 Vpp sine wave V <sub>IS</sub> = 5.0 Vpp sine wave	3.3 4.5 5.5	0.20 0.10 0.06	%

<sup>1.</sup> CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC} \cdot C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_{D} = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .

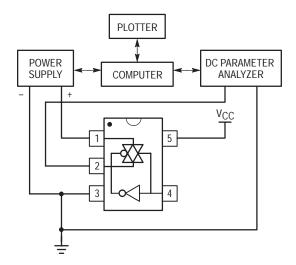


Figure 1. On Resistance Test Set-Up

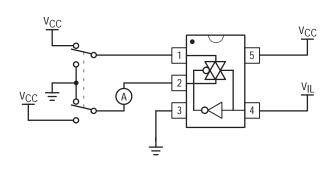


Figure 2. Maximum Off-Channel Leakage Current Test Set-Up

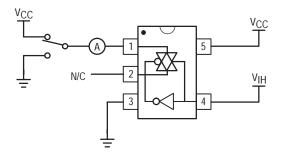


Figure 3. Maximum On-Channel Leakage Current Test Set-Up

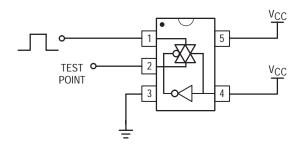


Figure 4. Propagation Delay Test Set-Up

Switch to Position 1 when testing tpLZ and tpZL Switch to Position 2 when testing tpHZ and tpZH

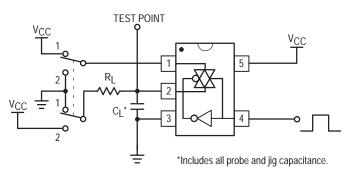


Figure 5. Propagation Delay Output Enable/Disable Test Set-Up

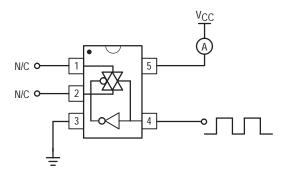
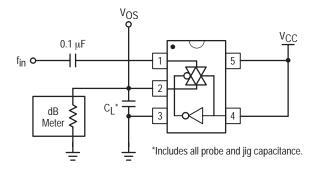


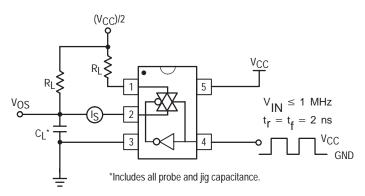
Figure 6. Power Dissipation Capacitance Test Set-Up



 $V_{\rm IS}$   $V_{\rm OS}$   $V_{\rm CC}$   $V_{\rm CC}$ 

Figure 7. Maximum On-Channel Bandwidth
Test Set-Up

Figure 8. Off-Channel Feedthrough Isolation Test Set-Up



To Distortion Meter  $\begin{array}{c} V_{CC} \\ V_{OS} \\ C_{L} \end{array}$   $\begin{array}{c} V_{IS} \\ \hline \\ \end{array}$   $\begin{array}{c} V_{IS} \\ \hline \\ \end{array}$   $\begin{array}{c} V_{CC} \\ \hline \\ \end{array}$ 

Figure 9. Feedthrough Noise, ON/OFF Control to Analog Out, Test Set-Up

Figure 10. Total Harmonic Distortion Test Set-Up

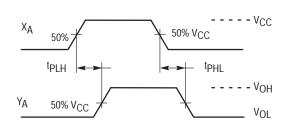


Figure 11. Propagation Delay, Analog In to Analog Out Waveforms

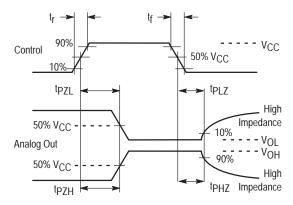


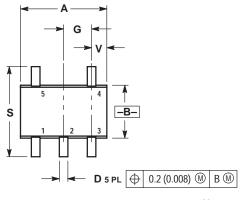
Figure 12. Propagation Delay, ON/OFF Control

#### **DEVICE ORDERING INFORMATION**

	Device Nomenclature							
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1G66DFT1	MC	74	VHC1G	66	DF	T1	SC-88A / SOT-353	7–Inch/3000 Unit

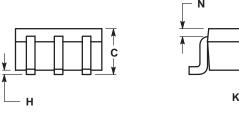
#### **PACKAGE DIMENSIONS**

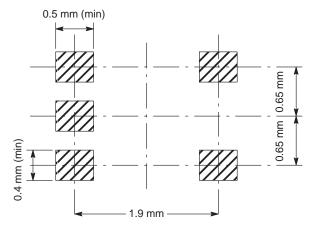
SC-88A / SOT-353 **DF SUFFIX** 5-LEAD PACKAGE CASE 419A-01 ISSUE B



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MIN MAX		MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40





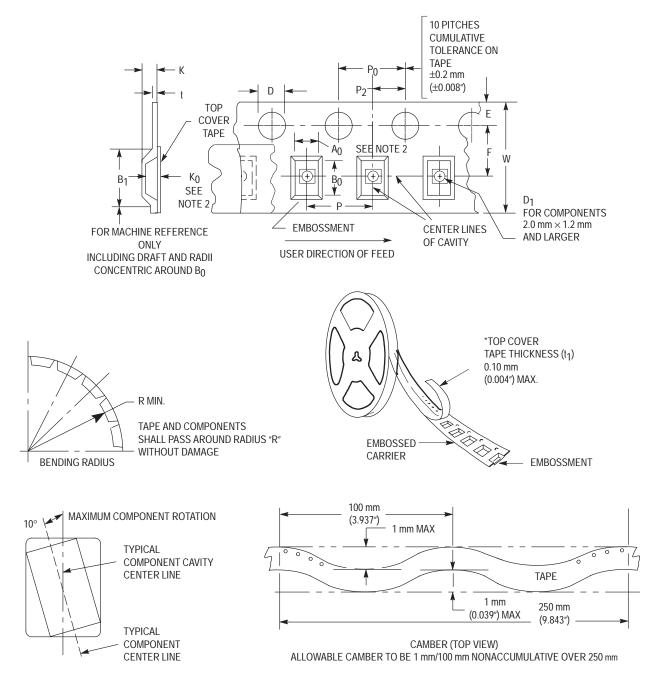


Figure 13. Carrier Tape Specifications

#### EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	E	F	К	Р	P <sub>0</sub>	P <sub>2</sub>	R	Т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

Metric Dimensions Govern–English are in parentheses for reference only.
 A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

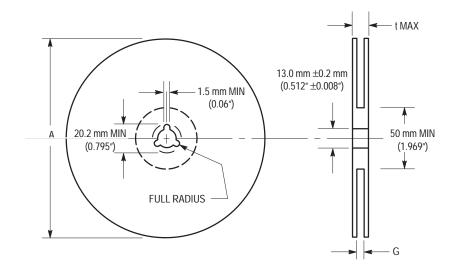
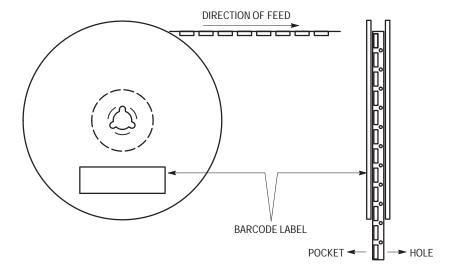


Figure 14. Reel Dimensions

#### **REEL DIMENSIONS**

Tape Size	A Max	G	t Max
8 mm	330 mm	8.400 mm, +1.5 mm, -0.0	14.4 mm
	(13")	(0.33", +0.059", -0.00)	(0.56")



**Figure 15. Reel Winding Direction** 

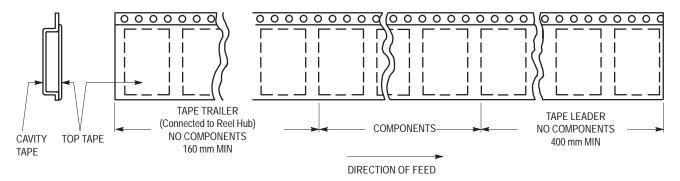


Figure 16. Tape Ends for Finished Goods

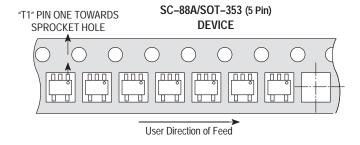


Figure 17. Reel Configuration

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